

N-channel 120 V 6.7 mΩ standard level MOSFET in TO-220 7 June 2013 Product data sheet

1. General description

Standard level N-channel MOSFET in TO-220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic power supply equipment.

2. Features and benefits

- High efficiency due to low switching and conduction losses
- Improved dynamic avalanche performance
- Suitable for standard level gate drive
- TO-220 package can be mounted to heatsink

3. Applications

- AC-to-DC power supply
- Synchronous rectification
- Motor control

4. Quick reference data

Table 1. Qu	lick reference data						
Symbol	Parameter	Conditions	N	lin	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-		-	120	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>	-		-	70	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-		-	405	W
Static charac	cteristics	•					
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 12	4		5.7	6.7	mΩ
Dynamic cha	aracteristics	·				1	
Q _{GD}	gate-drain charge	V_{GS} = 10 V; I _D = 25 A; V _{DS} = 60 V;	-		61.9	-	nC
Q _{G(tot)}	total gate charge	Fig. 14; Fig. 15	-		207.1	-	nC
Avalanche ru	uggedness						
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \; V; \; T_{j(\text{init})} = 25 \; ^{\circ}\text{C}; \; I_{D} = 70 \; A; \\ V_{sup} \leq 120 \; V; \; \text{unclamped}; \; R_{GS} = 50 \; \Omega; \\ \hline \text{Fig. 3} \end{array}$	-		-	532	mJ

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain	$2 \circ 4$	
3	S	source		G C C
mb	D	drain		mbb076 S
			$\begin{bmatrix} 1 \\ 1 \\ 2 \\ 3 \end{bmatrix}$	
			TO-220AB (SOT78)	

6. Ordering information

Table 3. Ordering information								
Type number	Package							
	Name	Description	Version					
PSMN6R3-120PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78					

7. Limiting values

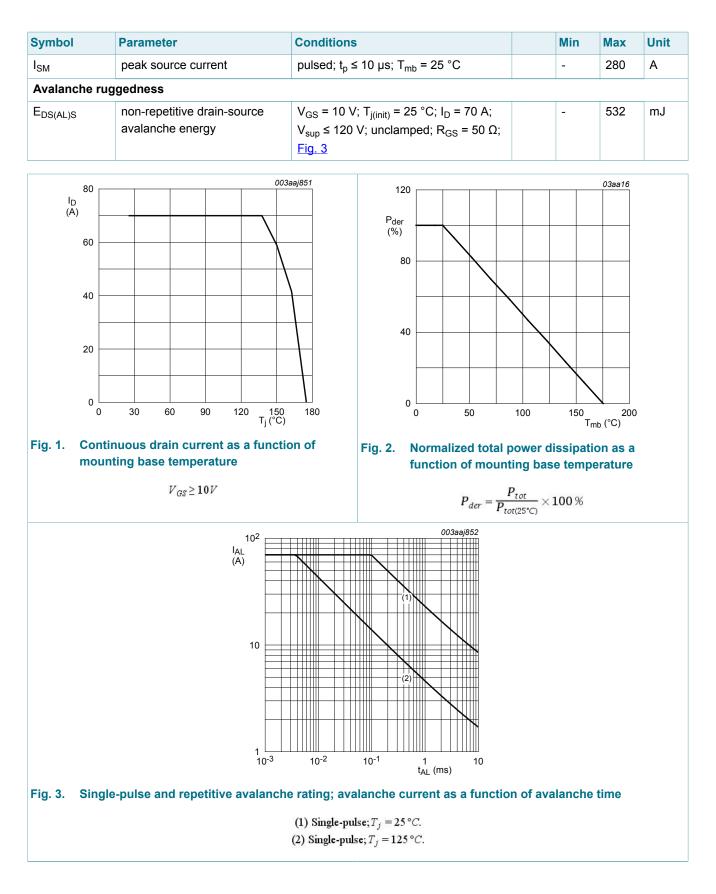
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	120	V
V _{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	120	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>	-	70	А
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 1</u>	-	70	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 4	-	280	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	405	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
$T_{sld(M)}$	peak soldering temperature		-	260	°C
Source-dra	in diode	· · ·	·		
I _S	source current	T _{mb} = 25 °C	-	70	А
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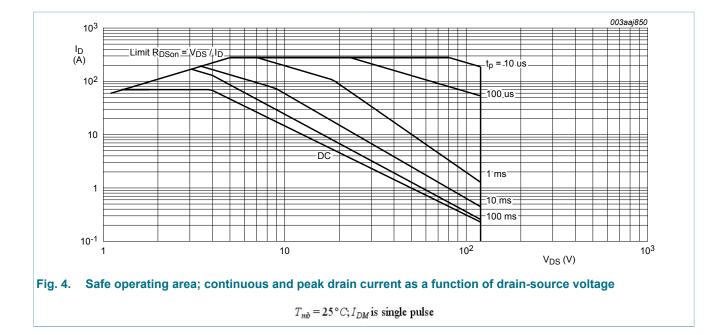
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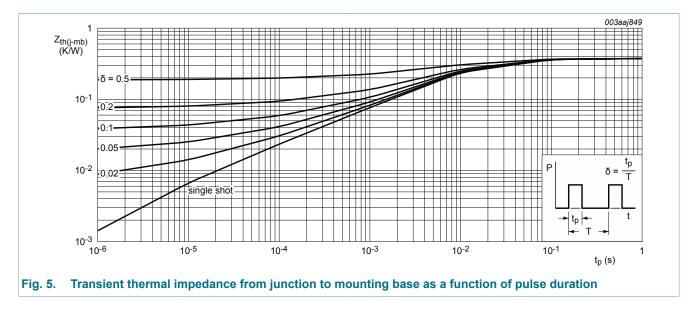
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8. Thermal characteristics

Table 5. Thermal characteristics								
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit	
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. <u>5</u>		-	0.3	0.37	K/W	
R _{th(j-a)}	thermal resistance from junction to ambient	vertical in free air		-	60	-	K/W	



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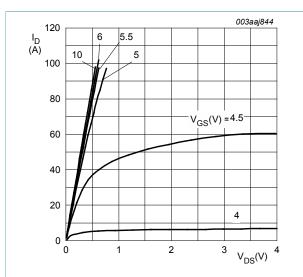
9. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	octeristics					
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	120	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	108	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 10; Fig. 11	2	3	4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10; Fig. 11	1	-	-	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; Fig. 10; Fig. 11	-	-	4.6	V
I _{DSS}	drain leakage current	V _{DS} = 120 V; V _{GS} = 0 V; T _j = 25 °C	-	0.1	1	μA
		V _{DS} = 120 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 12	4	5.7	6.7	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 13; Fig. 12	-	16.5	19.4	mΩ
R _G	internal gate resistance (AC)	f = 1 MHz	0.44	0.88	1.76	Ω
Dynamic ch	aracteristics	· · · ·			1	
Q _{G(tot)}	total gate charge	I_D = 25 A; V_{DS} = 60 V; V_{GS} = 10 V;	-	207.1	-	nC
Q _{GS}	gate-source charge	<u>Fig. 14; Fig. 15</u>	-	43.2	-	nC
Q _{GS(th)}	pre-threshold gate- source charge		-	29.8	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge		-	13.4	-	nC
Q _{GD}	gate-drain charge		-	61.9	-	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 25 A; V _{DS} = 60 V; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	4.3	-	V
C _{iss}	input capacitance	V _{DS} = 60 V; V _{GS} = 0 V; f = 1 MHz;	-	11384	-	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 16</u>	-	534	-	pF
C _{rss}	reverse transfer capacitance		-	358	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 60 V; R _L = 2.4 Ω; V _{GS} = 10 V;	-	42.1	-	ns
t _r	rise time	R _{G(ext)} = 5 Ω; T _j = 25 °C	-	58.2	-	ns

PSMN6R3-120PS

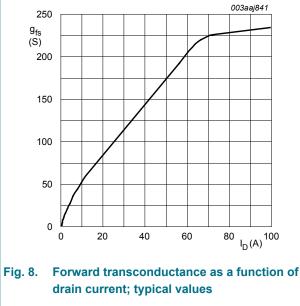
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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
t _{d(off)}	turn-off delay time			-	142.1	-	ns
t _f	fall time			-	67.7	-	ns
Source-drain diode							
V _{SD}	source-drain voltage	I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 17</u>		-	0.79	1.2	V
t _{rr}	reverse recovery time	$I_{\rm S}$ = 25 A; dI_{\rm S}/dt = -100 A/µs; V_{GS} = 0 V;		-	76.1	-	ns
Q _r	recovered charge	V _{DS} = 60 V		-	264.2	-	nC

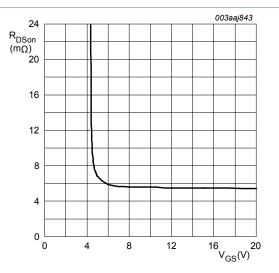




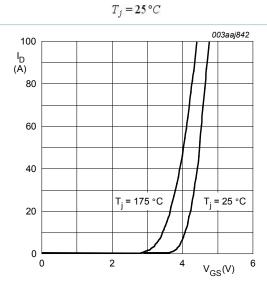




 $T_j = 25 \,^{\circ}C; V_{DS} = 10 \, V$





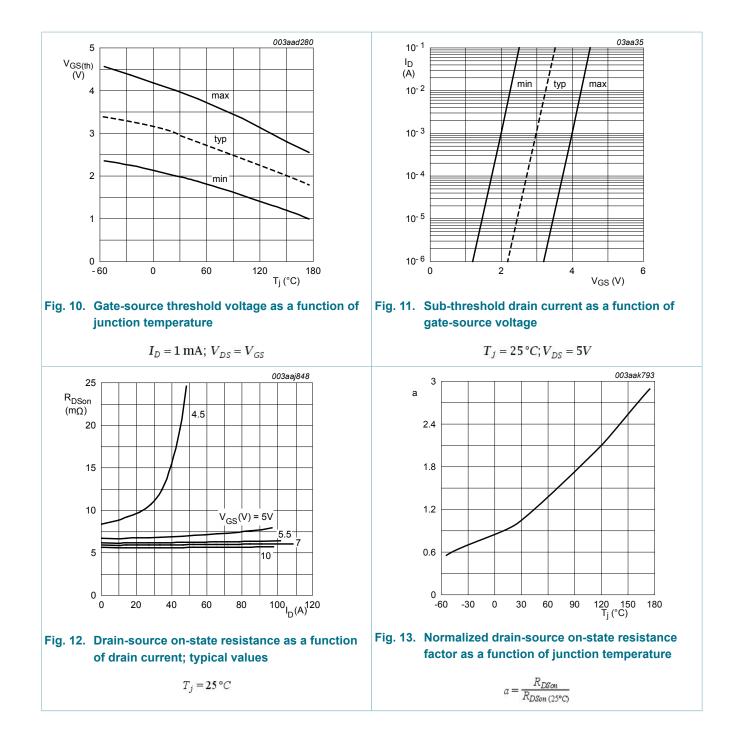




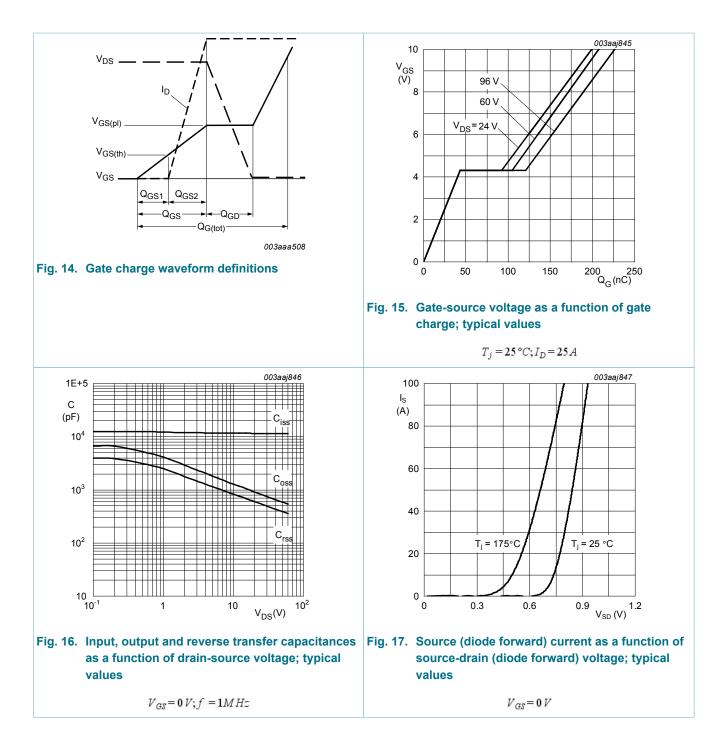
 $V_{DS} > I_D \times R_{DSon}$

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N-channel 120 V 6.7 m Ω standard level MOSFET in TO-220

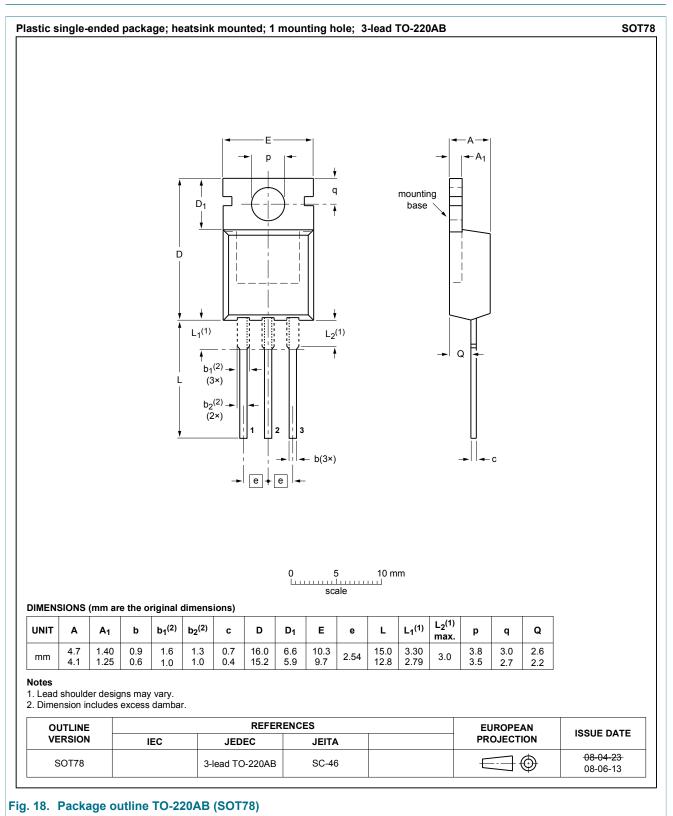


N-channel 120 V 6.7 mΩ standard level MOSFET in TO-220



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10. Package outline



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N-channel 120 V 6.7 mΩ standard level MOSFET in TO-220

11. Legal information

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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N-channel 120 V 6.7 m Ω standard level MOSFET in TO-220

12. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Limiting values	2
8	Thermal characteristics	4
9	Characteristics	5
10	Package outline	9
11	Legal information	10
11.1	Data sheet status	10
11.2	Definitions	10
11.3	Disclaimers	10
11.4	Trademarks	

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